

ABSTRACT OF THE DISCLOSURE

The invention includes improving or enhancing exchange coupling within a thin film layer. The improvement or enhancement to the exchange coupling occurs between the grains that are deposited to form the thin film. The improvement or enhancement to the exchange coupling between the grains of the thin film results from annealing the thin film at an elevated temperature for a period of time. A thin film structure and/or a magnetic recording layer made in accordance with the invention are disclosed.